# NEC Electronics Inc.

# μPD42S64400, 42S65400 16,777,216 x 4-Bit Dynamic CMOS RAM

# Preliminary

September 1993

## Description

The  $\mu$ PD42S64400 and  $\mu$ PD42S65400 are 64M-bit dynamic RAMs organized as 16,777,216 words by 4 bits. They are designed to operate from a single +3.3-volt power supply and have an optional fast-page mode.

Advanced polycide technology minimizes silicon areas and provides high storage cell capacity, high performance, and high reliability. A single-transistor dynamic storage cell and advanced CMOS circuitry throughout ensure minimum power dissipation, while an on-chip circuit internally generates the negative voltage substrate bias—automatically and transparently.

The three-state outputs are controlled by  $\overline{\text{CAS}}$  independent of  $\overline{\text{RAS}}$ . After a valid read or read-modify-write cycle, data is held on the outputs by maintaining  $\overline{\text{CAS}}$  low. Data outputs return to high impedance when  $\overline{\text{CAS}}$  goes high. Fast-page read and write cycles can be executed by cycling  $\overline{\text{CAS}}$ .

Refreshing may be accomplished by a CAS before RAS cycle that internally generates the refresh address. Refreshing can also be accomplished by RAS-only refresh cycles or by normal read or write cycles during a 256-ms refresh period.

Two versions of the 16M x 4-bit DRAM are available. The  $\mu$ PD42S64400 uses 8192 combinations of A<sub>0</sub> - A<sub>12</sub> for

 $\overline{\text{RAS}}$ -only refreshing and 4096 address combinations of A<sub>0</sub> - A<sub>11</sub> to perform  $\overline{\text{CAS}}$  before  $\overline{\text{RAS}}$  and hidden refreshing of the memory during a 256-ms period. The  $\mu\text{PD42S65400}$  uses 4096 address combinations of A<sub>0</sub> - A<sub>11</sub> during a 256-ms period for all refresh modes.

The  $\mu$ PD42S64400 and  $\mu$ PD42S65400 are available in a 34-pin plastic SOJ and 34-pin plastic TSOP.

#### **Features**

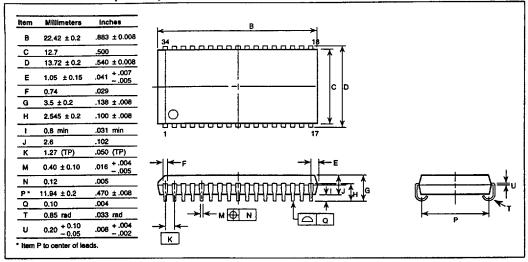
- □ 16,777,216 x 4-bit organization
- □ Single +3.3-volt power supply
- □ Fast-page option
- □ Low power dissipation: 0.72 mW (max) standby
- □ CAS before RAS refresh and self-refresh cycles
- Multiplexed address inputs
- On-chip substrate bias generator
- TTL-compatible inputs and outputs
- Nonlatched, three-state outputs
- Low input capacitance
- 34-pin plastic SOJ and TSOP packaging

#### **Ordering Information**

Part Number		Access Time (max)	R/W Cycle (max)	Fast-Page Cycle (max)	Active Power (max)	Package
μPD42S64400LG	i-A50	50 ns	90 ns	35 ns	360 mW	34-pin plastic SOJ
	-A60	60 ns	110 ns	40 ns	324 mW	•
	-A70	70 ns	130 ns	45 ns	288 mW	•
	-A80	80 ns	150 ns	50 ns	252 mW	
μPD42S64400G7	-A50	50 ns	90 ns	35 ns	360 mW	34-pin plastic TSOF
	-A60	60 ns	110 ns	40 ns	324 mW	•
	-A70	70 ns	130 ns	45 ns	288 mW	_
	-A80	80 ns	150 ns	50 ns	252 mW	
μPD42S65400LG	-A50	50 ns	90 ns	35 ns	468 mW	34-pin plastic SOJ
	-A60	60 ns	110 ns	40 ns	396 mW	
	-A70	70 ns	130 ns	45 ns	360 mW	
	-A80	80 ns	150 ns	50 ns	324 mW	
μPD42S65400G7	-A50	50 ns	90 ns	35 ns	468.mW	34-pin plastic TSOF
	-A60	60 ns	110 ns	40 ns	396 mW	
	-A70	70 ns	130 ns	45 ns	360 mW	-
	-A80	80 ns	150 ns	50 ns.	324 mW	-

# μPD42S64400, 42S65400

### 34-Pin Plastic SOJ (500-mil)



#### SOJ or TSOP 34 □ V<sub>SS</sub> 33 □ VO<sub>8</sub> **10**1 □ VO2 ☐ 3 32 1 VO7 VO3 4 31 1 VO6 104 □ 5 30 🗀 1/05 29 V<sub>SS</sub> 28 CAS NC □ 6 Voc□7 27 D 0E を 口8 RAS 0 9 26 🗀 NC NC 🗆 10 25 A A 12 A<sub>0</sub> 🗖 11 24 A11 23 A 10 A1 12 A2 13 22 A9 A3 🗖 14 21 Ag A<sub>4</sub> 🗖 15 20 A7 A5 16 19 A A 6 18 🗅 V<sub>SS</sub> ۷<sub>СС</sub> □ 17

A<sub>0</sub> to A<sub>11</sub>(A<sub>12</sub>) Address inputs 1/01 to 1/08 Data inputs/outputs RAS Row address strobe CAS Column address strobe ᄦ Write enable ÖE Output enable Vcc Supply voltage Ground V<sub>SS</sub> No connection

### 34-Pin Plastic TSOP (500 mil)

m	Millimeters	Inches	34 18 Enlarged detail of lead end
Α	22.66 max	.893 max	
ŗ	120 max	.048 max	
	1.27 (TP)	.050 (TP)	
	0.40 ± 0.10	.016 ± .004	<del></del>
	0.05 ± 0.05	.002 ± .002	E 5°±5°
F	1.10 max	.044 max	
G	0.97	.038	
H	14.3 ± 0.2	.563 ± 0.008	
1	12.7 ± 0.1	.500 ± 0.004	
J	0.8 ± 0.2	.031 ± .008	<del>&lt;</del>
ĸ	0.125 + 0.10 - 0.05	.005 + .004 002	^ J→
L	0.5 ± 0.1	.020 + .004 005	
M	0.21	.009	
N	0.10	.004	
			D

# NEC **NEC Electronics Inc.** CORPORATE HEADQUARTERS

475 Ellis Street P.O. Box 7241 Mountain View, CA 94039 TEL 415-960-6000

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or FAX your request to: 1-800-729-9288

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